

# **MAGNETORESISTIVE MEMORY DEVICE AND METHOD FOR FABRICATING THE SAME**

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## **ABSTRACT OF THE DISCLOSURE**

Embodiments of the invention include magnetoresistive memory cells having magnetic focusing spacers are formed on sidewalls thereof. Therefore, magnetic fields generated by a bit line and a digit line are focused by the magnetic focusing spacers and efficiently transferred to the magnetoresistive memory cell. In addition, an interlayer  
10 dielectric layer surrounding the magnetoresistive memory cell may be formed of high permeability material, thereby efficiently transferring magnetic field.